INTEGRATED CIRCUITS



Product specification Supersedes data of 1995 Apr 17 IC23 Data Handbook 1998 Jun 08





74ABT648

FEATURES

- Combines 74ABT245 and 74ABT374 type functions in one device
- Independent registers for A and B buses
- Multiplexed real-time and stored data
- Output capability: +64mA/-32mA
- Power-up 3-state
- Power-up reset
- Live insertion/extraction permitted
- Latch-up protection exceeds 500mA per Jedec Std 17
- ESD protection exceeds 2000 V per MIL STD 883 Method 3015 and 200 V per Machine Model

DESCRIPTION

The 74ABT648 high-performance BiCMOS device combines low static and dynamic power dissipation with high speed and high output drive.

QUICK REFERENCE DATA

The 74ABT648 transceiver/register consists of bus transceiver circuits with inverting 3-State outputs, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the input bus or the internal registers. Data on the A or B bus will be clocked into the registers as the appropriate clock pin goes High. Output Enable (\overline{OE}) and DIR pins are provided to control the transceiver function. In the transceiver mode, data present at the high impedance port may be stored in either the A or B register or both.

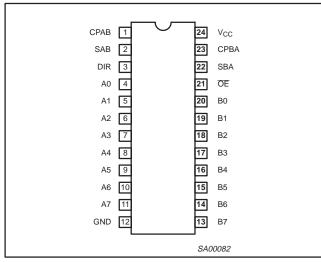
The Select (SAB, SBA) pins determine whether data is stored or transferred through the device in real–time. The DIR determines which bus will receive data when the \overline{OE} is active (Low). In the isolation mode (\overline{OE} = High), data from Bus A may be stored in the B register and/or data from Bus B may be stored in the A register. Outputs from real-time, or stored registers will be inverted. When an output function is disabled, the input function is still enabled and may be used to store and transmit data. Only one of the two buses, A or B may be driven at a time. The examples on the next page demonstrate the four fundamental bus management functions that can be performed with the 74ABT648.

SYMBOL	PARAMETER	CONDITIONS T _{amb} = 25°C; GND = 0V	TYPICAL	UNIT
t _{PLH} t _{PHL}	Propagation delay An to Bn or Bn to An	$C_L = 50 pF; V_{CC} = 5V$	5.9	ns
C _{IN}	Input capacitance CP, S, OE, DIR	$V_I = 0V \text{ or } V_{CC}$	4	pF
C _{I/O}	I/O capacitance	Outputs disabled; $V_O = 0V$ or V_{CC}	7	pF
I _{CCZ}	Total supply current	Outputs disabled; V _{CC} =5.5V	110	μΑ

ORDERING INFORMATION

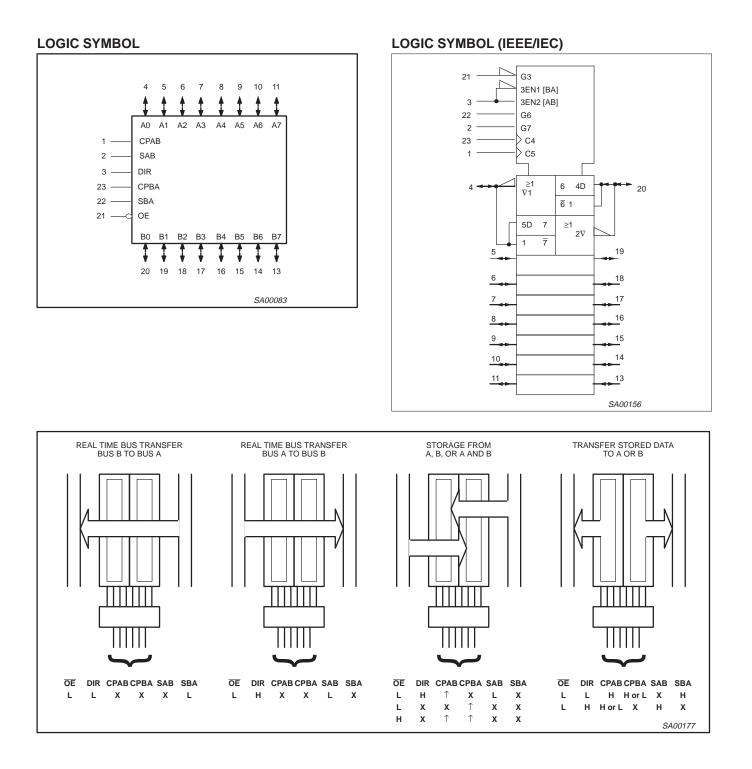
PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	DWG NUMBER
24-Pin Plastic DIP	–40°C to +85°C	74ABT648 N	74ABT648 N	SOT222-1
24-Pin plastic SO	-40°C to +85°C	74ABT648 D	74ABT648 D	SOT137-1
24-Pin Plastic SSOP Type II	-40°C to +85°C	74ABT648 DB	74ABT648 DB	SOT340-1
24-Pin Plastic TSSOP Type I	-40°C to +85°C	74ABT648 PW	74ABT648PW DH	SOT355-1

PIN CONFIGURATION



PIN DESCRIPTION

PIN NUMBER	SYMBOL	FUNCTION
1, 23	CPAB / CPBA	A to B clock input / B to A clock input
2, 22	SAB / SBA	A to B select input / B to A select input
3	DIR	Direction control input
4, 5, 6, 7, 8, 9, 10, 11	A0 – A7	Data inputs/outputs (A side)
20, 19, 18, 17, 16, 15, 14, 13	B0 – B7	Data inputs/outputs (B side)
21	ŌĒ	Output enable input (active-Low)
12	GND	Ground (0V)
24	V _{CC}	Positive supply voltage



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FUNCTION TABLE

		INPUT	6			DAT	a I/o	OPERATING MODE
ŌĒ	DIR	СРАВ	СРВА	SAB	SBA	An	Bn	
х	х	Ŷ	Х	х	Х	Input	Unspecified output*	Store A, B unspecified
Х	х	х	\uparrow	х	Х	Unspecified output*	Input	Store B, A unspecified
H H	X X	↑ H or L	↑ H or L	X X	X X	Input	Input	Store A and B data Isolation, hold storage
L L	L	X X	X H or L	X X	L H	Output	Input	Real time \overline{B} data to A bus Stored \overline{B} data to A bus
L	H H	X H or L	X X	L H	X X	Input	Output	Real time \overline{A} data to B bus Stored \overline{A} data to B bus

H = High voltage level L = Low voltage level

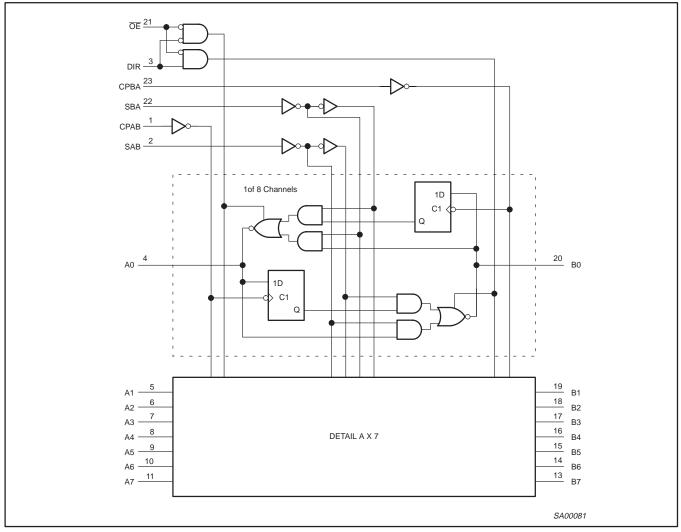
L X ↑

= Don't care

=

Low-to-High clock transition The data output function may be enabled or disabled by various signals at the OE input. Data input functions are always enabled, i.e., data at the bus pins will be stored on every Low-to-High transition of the clock.

LOGIC DIAGRAM



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ABSOLUTE MAXIMUM RATINGS^{1, 2}

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V _{CC}	DC supply voltage		-0.5 to +7.0	V
I _{IK}	DC input diode current	V ₁ < 0	-18	mA
VI	DC input voltage ³		-1.2 to +7.0	V
I _{OK}	DC output diode current	V _O < 0	-50	mA
V _{OUT}	DC output voltage ³	output in Off or High state	-0.5 to +5.5	V
I _{OUT}	DC output current	output in Low state	128	mA
T _{stg}	Storage temperature range		-65 to 150	°C

NOTES:

1. Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

 The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.

3. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIM	ITS	UNIT
		Min	Max	
V _{CC}	DC supply voltage	4.5	5.5	V
VI	Input voltage	0	V _{CC}	V
V _{IH}	High-level input voltage	2.0		V
V _{IL}	Low-level Input voltage		0.8	V
I _{ОН}	High-level output current		-32	mA
I _{OL}	Low-level output current		64	mA
Δt/Δv	Input transition rise or fall rate	0	10	ns/V
T _{amb}	Operating free-air temperature range	-40	+85	°C

DC ELECTRICAL CHARACTERISTICS

						LIMITS			
SYMBOL	PARAN	IETER	TEST CONDITIONS	Tai	_{mb} = +25	°C	T _{amb} = to +8	UNIT	
				Min	Тур	Max	Min	Max	
V _{IK}	Input clamp vo	ltage	$V_{CC} = 4.5V; I_{IK} = -18mA$		-0.9	-1.2		-1.2	V
			V_{CC} = 4.5V; I_{OH} = –3mA; V_{I} = V_{IL} or V_{IH}	2.5	3.2		2.5		V
V _{OH}	High-level outp	out voltage	V_{CC} = 5.0V; I_{OH} = –3mA; V_{I} = V_{IL} or V_{IH}	3.0	3.7		3.0		V
			V_{CC} = 4.5V; I_{OH} = -32mA; V_I = V_{IL} or V_{IH}	2.0	2.3		2.0		V
V _{RST}	Power-up outp voltage ³	ut low	V_{CC} = 5.5V; I_{O} = 1mA; V_{I} = GND or V_{CC}		0.13	0.55		0.55	V
V _{OL}	Low-level outp	ut voltage	V_{CC} = 4.5V; I_{OL} = 64mA; V_I = V_{IL} or V_{IH}		0.42	0.55		0.55	V
I _{OFF}	Power-off leaka	age current	V_{CC} = 0.0V; V _I or V _O \leq 4.5V		±5.0	±100		±100	μΑ
I _{PU/} PD	Power–up/dow output current ⁴		V_{CC} = 2.1V; V_O = 0.5V; V_I = GND or V_{CC} ; V_{OE} = Don't care		±5.0	±50		±50	μΑ
I	Input leakage	Control pins	V_{CC} = 5.5V; V_I = GND or 5.5V		±0.01	±1.0		±1.0	μΑ
	current	Data pins	V_{CC} = 5.5V; V_I = GND or 5.5V		±5	±100		±100	μΑ
I _{IH} + I _{OZH}	3-State output	High current	V_{CC} = 5.5V; V_{O} = 2.7V; V_{I} = V_{IL} or V_{IH}		5.0	50		50	μΑ
I _{IL} + I _{OZL}	3-State output	Low current	V_{CC} = 5.5V; V_{O} = 0.5V; V_{I} = V_{IL} or V_{IH}		-5.0	-50		-50	μΑ
I _{CEX}	Output high lea	akage current	V_{CC} = 5.5V; V_{O} = 5.5 V; V_{I} = GND or V_{CC}		5.0	50		50	μΑ
Ι _Ο	Output current	1	$V_{CC} = 5.5V; V_{O} = 2.5V$	-50	-65	-180	-50	-180	mA
I _{CCH}			V_{CC} = 5.5V; Outputs High, V_I = GND or V_{CC}		110	250		250	μA
I _{CCL}	Quiescent supp	ply current	V_{CC} = 5.5V; Outputs Low, V_I = GND or V_{CC}		20	30		30	mA
I _{CCZ}			V_{CC} = 5.5V; Outputs 3-State; V _I = GND or V _{CC}		110	250		250	μA
ΔI_{CC}	Additional supp input pin ²	oly current per	V_{CC} = 5.5V; one input at 3.4V, other inputs at V _{CC} or GND; V _{CC} = 5.5V		0.3	1.5		1.5	mA

NOTES:

Not more than one output should be tested at a time, and the duration of the test should not exceed one second.
This is the increase in supply current for each input at 3.4V.
For valid test results, data must not be loaded into the flip-flops (or latches) after applying the power.
This parameter is valid for any V_{CC} between 0V and 2.1V, with a transition time of up to 10msec. From V_{CC} = 2.1 to V_{CC} = 5V ± 10% a transition time of up to 100µsec is permitted.

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AC CHARACTERISTICS

GND = 0V, t_{R} = t_{F} = 2.5ns, C_{L} = 50pF, R_{L} = 500 Ω

					LIMITS			
SYMBOL	PARAMETER	WAVEFORM	r i	Γ _{amb} = +25° V _{CC} = +5.0\	с /	+8	= -40 to 5°C .0V ±0.5V	UNIT
			Min	Тур Мах		Min	Max	
f _{MAX}	Maximum clock frequency	1	125	200		125		MHz
t _{PLH} t _{PHL}	Propagation delay CPAB to Bn or CPBA to An	1	2.2 1.7	5.3 5.9	6.8 7.4	2.2 1.7	7.8 8.4	ns
t _{PLH}	Propagation delay	2	1.0	3.6	5.1	1.0	6.1	ns
t _{PHL}	An to Bn or Bn to An	3	1.5	4.2	5.6	1.5	6.3	
t _{PLH}	Propagation delay	2	1.5	4.9	6.1	1.5	7.1	ns
t _{PHL}	SAB to Bn or SBA to An	3	1.5	5.4	6.9	1.5	7.7	
t _{PZH}	Output enable time	5	1.0	4.3	5.3	1.0	6.3	ns
t _{PZL}	OE to An or Bn	6	2.1	5.5	7.4	2.1	8.8	
t _{PHZ}	Output disable time	5	1.5	6.2	7.3	1.5	8.3	ns
t _{PLZ}	OE to An or Bn	6	1.5	6.0	7.0	1.5	7.5	
t _{PZH}	Output enable time	5	1.2	4.8	5.7	1.2	6.7	ns
t _{PZL}	DIR to An or Bn	6	2.5	6.0	9.0	2.5	9.5	
t _{PHZ}	Output disable time	5	1.5	5.9	6.7	1.5	7.7	ns
t _{PLZ}	DIR to An or Bn	6	1.5	6.3	7.2	1.5	8.2	

AC SETUP REQUIREMENTS

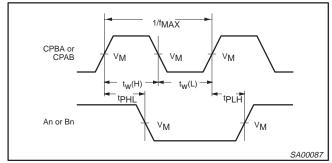
GND = 0V, t_R = t_F = 2.5ns, C_L = 50pF, R_L = 500 Ω

				NITS		
SYMBOL	PARAMETER	WAVEFORM	T _{amb} = V _{CC} =	= +25°C = +5.0V	T _{amb} = -40 to +85°C V _{CC} = +5.0V ±0.5V	UNIT
			Min	Тур	Min	
t _s (H) t _s (L)	Setup time An to CPAB, Bn to CPBA	4	3.0 3.0	1.5 1.0	3.0 3.0	ns
t _h (H) t _h (L)	Hold time An to CPAB, Bn to CPBA	4	0.0 0.0	-0.4 -1.0	0.0 0.0	ns
t _w (H) t _w (L)	Pulse width, High or Low CPAB or CPBA	1	3.5 4.0	2.6 1.0	3.5 4.0	ns

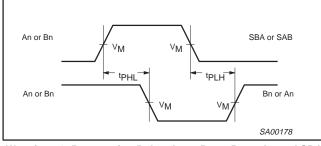
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AC WAVEFORMS

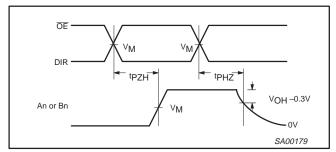
 V_{M} = 1.5V, V_{IN} = GND to 3.0V



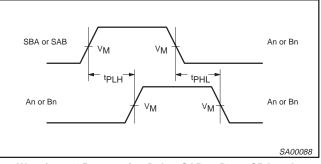
Waveform 1. Propagation Delay, Clock Input to Output, Clock Pulse Width, and Maximum Clock Frequency



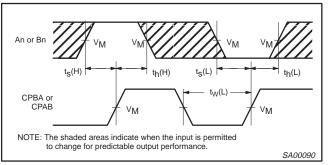
Waveform 3. Propagation Delay, An to Bn or Bn to An and SBA to An or SAB to Bn



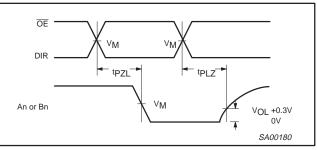
Waveform 5. 3-State Output Enable Time to High Level and Output Disable Time from High Level



Waveform 2. Propagation Delay, SAB to Bn or SBA to An



Waveform 4. Data Setup and Hold Times

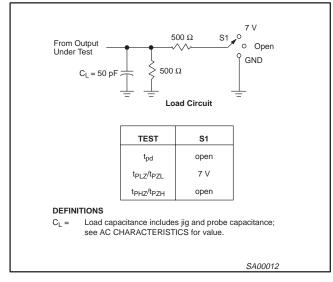


Waveform 6. 3-State Output Enable Time to Low Level and Output Disable Time from Low Level

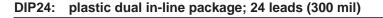
Product specification

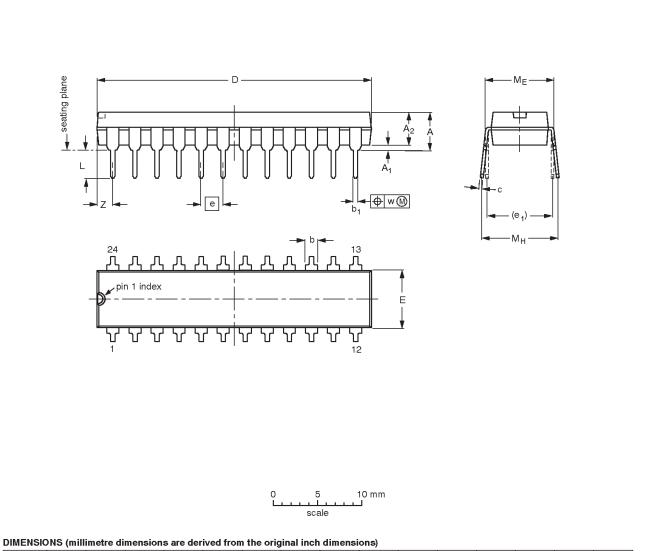
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TEST CIRCUIT AND WAVEFORM



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UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	с	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	L	M _E	М _Н	w	Z ⁽¹⁾ max.
mm	4.70	0.38	3.94	1.63 1.14	0.56 0.43	0.36 0.25	31.9 31.5	6.73 6.48	2.54	7.62	3.51 3.05	8.13 7.62	10.03 7.62	0.25	2.05
inches	0.185	0.015	0.155	0.064 0.045	0.022 0.017	0.014 0.010	1.256 1.240	0.265 0.255	0.100	0.300	0.138 0.120	0.32 0.30	0.395 0.300	0.01	0.081

Note

1. Plastic or metal protrusions of 0.01 inches maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE
SOT222-1		MS-001AF			95-03-11

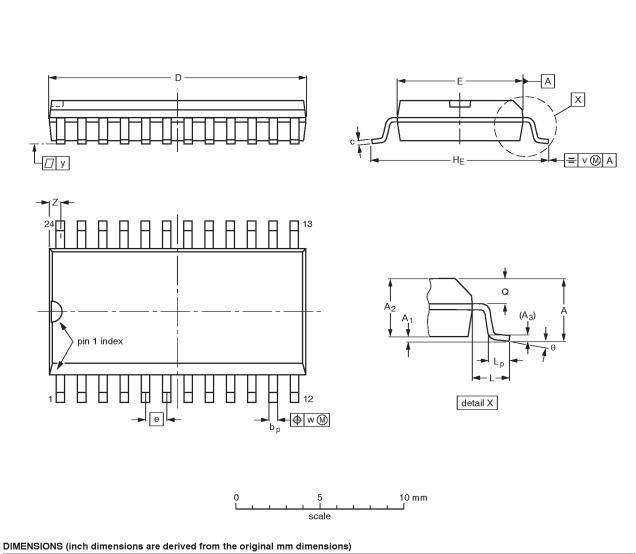
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SOT222-1

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Octal bus transceiver/register, inverting (3-State)

SO24: plastic small outline package; 24 leads; body width 7.5 mm



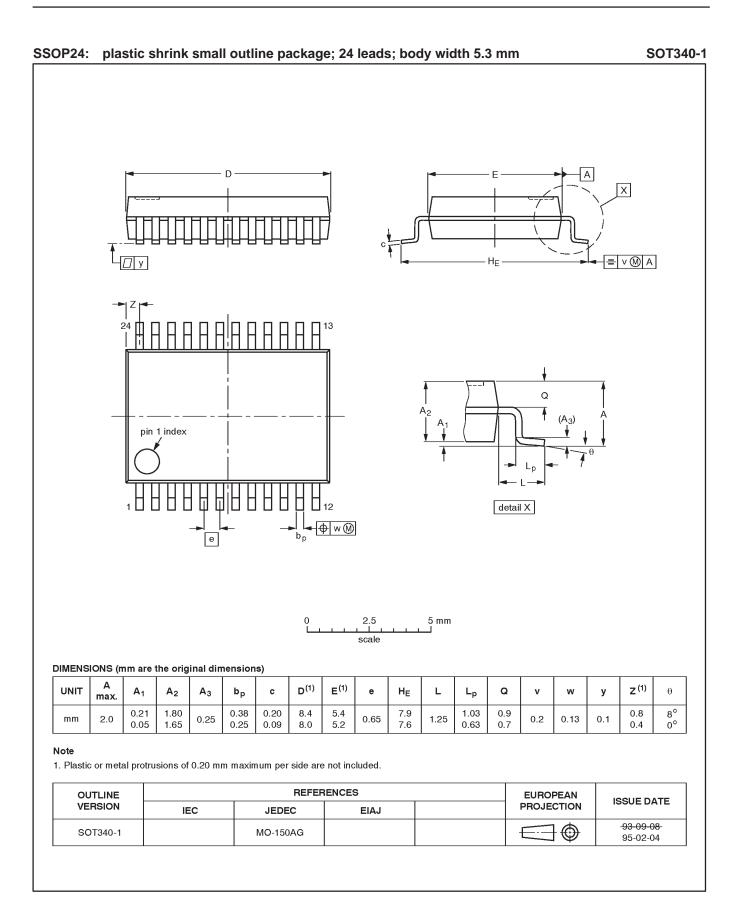
UNIT	A max.	A ₁	A ₂	Α3	b _p	с	D ⁽¹⁾	E ⁽¹⁾	e	Η _E	L	Lp	Q	v	v	У	z ⁽¹⁾	θ
mm	2.65	0.30 0.10	2.45 2.25	0.25	0.49 0.36	0.32 0.23	15.6 15.2	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8°
inches	0.10	0.012 0.004	0.096 0.089	0.01	0.019 0.014	0.013 0.009	0.61 0.60	0.30 0.29	0.050	0.42 0.39	0.055	0.043 0.016	0.043 0.039	0.01	0.01	0.004	0.035 0.016	0°

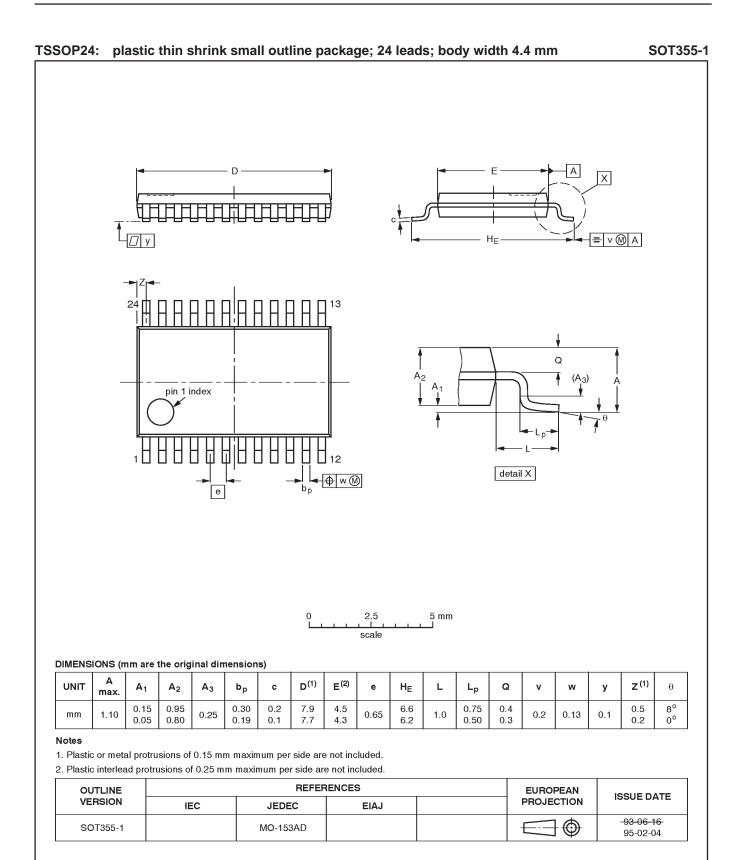
Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN	ISSUE DATE
	IEC	JEDEC	EIAJ		PROJECTION	1550E DATE
SOT137-1	075E05	MS-013AD				-92-11-17 95-01-24

SOT137-1





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Data sheet status

Data sheet status	Product status	Definition [1]
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make chages at any time without notice in order to improve design and supply the best possible product.
Product specification	Production	This data sheet contains final specifications. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.

[1] Please consult the most recently issued datasheet before initiating or completing a design.

Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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